Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H400S

APPLICATIONS

Low Frequency Power Amplifier.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····900mW

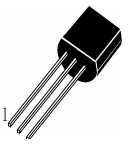
V_{CBO}——Collector-Base Voltage·····25V

V_{CEO}——Collector-Emitter Voltage·····25V

V_{EBO}——Emitter-Base Voltage·····5V

I_C——Collector Current·····1A

TO-92



1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	25			V	I_C=10μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	25			V	I_C=1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	I_E=10μA，I_C=0
H_{FE} (1)	DC Current Gain	60		560		V_{CE}=2V, I_C=50mA
H_{FE} (2)	DC Current Gain	30				V_{CE}=2V, I_C=1A
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.1	0.3	V	I_C=0.5A, I_B=50mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		0.85	1.2	V	I_C=0.5A, I_B=50mA
I_{CBO}	Collector Cut-off Current			1	μA	V_{CB}=20V, I_E=0
I_{EBO}	Emitter Cut-off Current			1	μA	V_{EB}=4V, I_C=0
I_{CEO}	Collector Cut-off Current			1	μA	V_{CE}=20V, I_B=0
f_T	Current Gain-Bandwidth Product		180		MHz	V_{CE}=10V, I_C=50mA
Cob	Output Capacitance		15		pF	V_{CB}=10V, I_E=0，f=1MHz

h_{FE} Classification

D	E	F	G
60—120	100—200	160—320	280—560